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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, CSIO, EBI/EMI, Ethernet, I ² C, LINbus, SmartCard, SPI, UART/USART, USB
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	153
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 32x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/s6e2g26jhagv2000a

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CYPRESS EMBEDDED IN TOMORROW

S6E2G Series

32-bit ARM[®] Cortex[®]-M4F FM4 Microcontroller

S6E2G Series are FM4 devices with up to 180 MHz CPU, 1 MB flash, 192 KB SRAM, 20x communication peripherals, 33x digital peripherals and 3x analog peripherals. They are designed for industrial automation and metering applications.

Devices in the S6E2G Series are highly integrated 32-bit microcontrollers with high performance and competitive cost. This series is based on the ARM Cortex-M4F processor with on-chip flash memory and SRAM. The series has peripherals such as motor control timers, A/D converters, and communications interfaces (USB, CAN, UART, CSIO (SPI), I²C, LIN). The products that are described in this data sheet are placed into TYPE5-M4 product categories in the "FM4 Family Peripheral Manual Main Part (002-04856)".

- 32-bit ARM Cortex-M4F Core □ Up to 180 MHz frequency operation
- On-chip Memories
 Flash memory: Up to 1024 Kbytes
 SRAM memory:
 - · SRAM0: up to 128 Kbytes
 - SRAM1: 32 Kbytes
 - SRAM2: 32 Kbytes
- Direct Memory Access (DMA) Controller (Eight Channels)
- Descriptor System Data Transfer Controller (DSTC); 256 channels
- External Bus Interface
- USB Interface (Max two channels): Host and Device
- CAN Interface (Max one channel) Available on S6E2GM and S6E2GH Devices Only
- Multi-function Serial Interface (Max 10 Channels)
 UART (Universal Asynchronous Receiver/Transmitter)
 Clock Synchronous Serial Interface (CSIO (SPI))
 Local Interconnect Network (LIN)
 Inter-Integrated Circuit (I²C)
 Inter-IC Sound (I²S)
- Base Timer (Max 16 channels)
- General Purpose I/O Port
 - □ Up to 121 high-speed general-purpose I/O ports in 144-pin package
 - □ Up to 153 high-speed general-purpose I/O ports in 176-pin package
- Multi-function Timer (Max two units)
- Real-Time Clock (RTC)
- Analog to Digital Converter (ADC) (Max 32 Channels)
- ■Dual Timer (32-/16-bit Down Counter)
- Quadrature Position/Revolution Counter (QPRC; Max two channels)

- Watch Counter
- External Interrupt Controller Unit
- Watchdog Timer (Two channels)
- Cyclic Redundancy Check (CRC) Accelerator
- SD Card Interface Available on S6E2GM, S6E2GH, and S6E2GK Devices Only
- Ethernet-MAC Available on S6E2GM, S6E2GK, and S6E2G2 Devices only
- Smartcard Interface (Max 2 channels)
- Five Clock Sources
- Six Reset Sources
- Clock Supervisor (CSV)
- Low-Voltage Detector (LVD)
- Six Low-power Consumption Modes
 Sleep
 Timer
 RTC
 Stop
 Deep standby RTC
 Deep standby stop
- Peripheral Clock Gating System
- Crypto Assist Function
- Debug
- □ Serial wire JTAG debug port (SWJ-DP)
- Embedded trace macrocells (ETM) provide comprehensive debug and trace facilities.
 AHB trace macrocells (HTM)
- 41-bit Unique ID
- Wide range voltage: VCC = 2.7 to 5.5 V



Pin Number		Din Nome	I/O Circuit	Pin State	
LQFP-176	LQFP-144	Pin Name	Туре	Туре	
		P3C			
		SIN2_1			
38	33	RTO03_0 (PPG03_0)	G	к	
		TIOA3_1			
		INT19_1			
		MAD21_0			
		P3D			
		SOT2_1 (SDA2_1)			
39	34	RTO04_0 (PPG04_0)	G	I.	
		TIOA4_1			
		MAD20_0			
		P3E			
		SCK2_1 (SCL2_1)		I.	
40	35	RTO05_0 (PPG05_0)	G		
		TIOA5_1			
		 MAD19_0			
		P5D	E		
	-	SIN1_1		К	
41		MI2SDI1_1			
		TIOB12_2			
		INT03_2			
		P5E			
42	-	SOT1_1 (SDA1_1)	Е	T	
		MI2SDO1_1			
		TIOA13_2			
		P5F			
43	-	SCK1_1 (SCL1_1)	E	I.	
_		MI2SCK1_1			
		TIOB13_2			
44	36	VSS	-	-	
45	37	VCC	-	-	
		P40			
		SIN7_1			
	_	RTO10_0 (PPG10_0)			
46	38	TIOA0_0	G	K	
		AIN0_0			
		INT23_0]		
		MCSX7_0			



Pin Number		Din Nama	I/O Circuit	Pin State
LQFP-176	LQFP-144	Pin Name	Туре	Туре
		P4E		
		SCK9_0 (SCL9_0)		
66	56	INT05_0	L	Q
		WKUP2	1	
		MCSX1_0	1	
		P70		
		ADTG_7	1	
67	57	SOT9_0 (SDA9_0)	L	I
		MCSX0_0	1	
		P71		
		ADTG_8	1	
68	58	SIN9_0	I	к
		INT04_1	1	
		MRDY_0	1	
		P72		
00	50	TIOB0_0		I.
69	59	INT06_2	E	
		MAD00_0	1	
		P73		
		SIN8_0		
70	60	TIOB1_0	E	К
		INT20_0		
		MAD01_0		
		P74		
71	61	SOT8_0 (SDA8_0)	Е	I
	0.	TIOB2_0		
		MAD02_0		
		P75		
72	62	SCK8_0 (SCL8_0)	Е	I.
		TIOB3_0		
		MAD03_0		
		P76		
		SIN6_0]	
73	63	TIOB4_0	Е	K
		INT21_0		
		MAD04_0		
		P77		
74	64	SOT6_0 (SDA6_0)	L	I
		TIOB5_0]	
1		MAD05_0]	





Pin N	umber	Din Nome	I/O	Pin State	
LQFP-176	LQFP-144	Pin Name	Туре	Туре	
		P78			
		SCK6_0			
75	65	(SCL6_0)	L	I	
		AIN0_1			
		MAD06_0			
		P79 SCS60.0			
76	66	BIND 1	_	K	
70	00			ĸ	
		MADOZ 0			
		SCS61_0			
77	67	ZINO 1	F	ĸ	
	07				
		MAD08.0			
		DE2			
		SCS62 0		I	
78	-	DTTI1X 1			
70					
			_		
	-	PE3			
		SCS63 0			
		ERCK1_1	Е		
79				K	
		INT05_1			
		PF4			
		IC10_1	_		
80	-	TIOA7 1	Е	К	
		INT06 1			
		IC1_VPEN_1			
		 PF5			
		SIN3_1	1		
		 IC11_1	_		
81	-	TIOB7_1	E	K	
		 INT07_1			
		IC1_RST_1	1		
		PF6			
		SOT3_1	1		
		(SDA3_1)		К	
82	-	IC12_1	E		
		TIOA14_1	_		
		INT20_1	_		
		IC1_DATA_1			





Pin Number		Din Nome	I/O	Pin State
LQFP-176	LQFP-144	Pin Name	Туре	Туре
		PB6		
112		AN22		
	-	SOT8_1 (SDA8_1)	F	Ν
		TIOA12_1		
		BIN1_2		
		TRACED14		
		PB7		
		AN23		
110		SCK8_1 (SCL8_1)	-	N
113	-	TIOB12_1	F	IN
		ZIN1_2		
		TRACED15		
		P1C		
		AN12		
114	90	SCK0_1 (SCL0_1)	F	Ν
		TIOA5 2		
		TRACECLK		
		P1D		
	91	AN13		
115		SOT0_1 (SDA0_1)	F	L
		MAD09_0		
		P1F		
		AN14		
		SIN0 1		
116	92	TIOA8 1	F	Μ
		 INT26_1		
		 MAD10_0		
		P1F		
		AN15		
		RTS5_0	_	
117	93	TIOB8_1	F	Μ
		INT27_1	1	
		MAD11_0	1	
		P2A		
		AN24		
118	94	CTS5_0	F	М
		INT08_2		
		MAD12_0		





Module Din Name		Eurotion	Pin Number		
Woulle	Fill Name	Function	LQFP 176	LQFP 144	
	MADATA00_0		2	2	
	MADATA01_0		3	3	
	MADATA02_0		4	4	
	MADATA03_0		5	5	
	MADATA04_0		6	6	
	MADATA05_0		7	7	
	MADATA06_0		8	8	
	MADATA07_0	External bus interface data bus	9	9	
	MADATA08_0	(address/data multiplex bus)	13	10	
	MADATA09_0		14	11	
	MADATA10_0		15	12	
	MADATA11_0		16	13	
	MADATA12_0		17	14	
	MADATA13_0		18	15	
	MADATA14_0		19	16	
	MADATA15_0		20	17	
	MDQM0_0	External bus interface byte mask signal	21	18	
	MDQM1_0	output pin	22	19	
	MALE_0	External bus interface address latch enable output signal for multiplex	171	139	
External	MRDY_0	External bus interface external RDY input signal	68	58	
546	MCLKOUT_0	External bus interface external clock output pin	23	20	
	MNALE_0	External bus interface ALE signal to control NAND flash output pin	97	81	
	MNCLE_0	External bus interface CLE signal to control NAND flash output pin	96	80	
	MNREX_0	External bus interface read enable signal to control NAND flash	94	78	
	MNWEX_0	External bus interface write enable signal to control NAND flash	95	79	
	MOEX_0	External bus interface read enable signal for SRAM	169	137	
	MWEX_0	External bus interface write enable signal for SRAM	170	138	
	MSDCLK_0	SDRAM interface SDRAM clock output pin	65	55	
	MSDCKE_0	SDRAM interface SDRAM clock enable pin	64	54	
	MRASX_0	SDRAM interface SDRAM row active strobe pin	60	50	
	MCASX_0	SDRAM interface SDRAM column active strobe pin	61	51	
	MSDWEX_0	SDRAM interface SDRAM write enable pin	62	52	







8. Handling Precautions

Every semiconductor device has a characteristic, inherent rate of failure. The possibility of failure is greatly affected by the conditions in which they are used (circuit conditions, environmental conditions, etc.). This page describes precautions that must be observed to minimize the chance of failure and to obtain higher reliability from your Cypress semiconductor devices.

8.1 Precautions for Product Design

This section describes precautions when designing electronic equipment using semiconductor devices.

Absolute Maximum Ratings

Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of certain established limits, called absolute maximum ratings. Do not exceed these ratings.

Recommended Operating Conditions

Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.

Always use semiconductor devices within the recommended operating conditions. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their sales representative beforehand.

Processing and Protection of Pins

These precautions must be followed when handling the pins that connect semiconductor devices to power supply and I/O functions.

1. Preventing Over-Voltage and Over-Current Conditions

Exposure to voltage or current levels in excess of maximum ratings at any pin is likely to cause deterioration within the device, and in extreme cases leads to permanent damage of the device. Try to prevent such overvoltage or over-current conditions at the design stage.

2. Protection of Output Pins

Shorting of output pins to supply pins or other output pins, or connection to large capacitance can cause large current flows. Such conditions, if present for extended periods of time, can damage the device; therefore, avoid this type of connection.

3. Handling of Unused Input Pins

Unconnected input pins with very high impedance levels can adversely affect stability of operation. Such pins should be connected through an appropriate resistance to a power-supply pin or ground pin.



Surface Mount Type

Surface mount packaging has longer and thinner leads than lead-insertion packaging, and therefore leads are more easily deformed or bent. The use of packages with higher pin counts and narrower pin pitch results in increased susceptibility to open connections caused by deformed pins, or shorting due to solder bridges.

You must use appropriate mounting techniques. Cypress recommends the solder reflow method, and has established a ranking of mounting conditions for each product. Users are advised to mount packages in accordance with Cypress ranking of recommended conditions.

Lead-Free Packaging

CAUTION: When ball grid array (BGA) packages with Sn-Ag-Cu balls are mounted using Sn-Pb eutectic soldering, junction strength may be reduced under some conditions of use.

Storage of Semiconductor Devices

Because plastic chip packages are formed from plastic resins, exposure to natural environmental conditions will cause absorption of moisture. During mounting, the application of heat to a package that has absorbed moisture can cause surfaces to peel, reducing moisture resistance and causing packages to crack. To prevent this, do the following:

- 1. Avoid exposure to rapid temperature changes, which can cause moisture to condense inside the product. Store products in locations where temperature changes are slight.
- Use dry boxes for product storage. Products should be stored below 70% relative humidity, and at temperatures between 5°C and 30°C.
- 3. When Dry Packages are opened, it is recommended to have humidity between 40% and 70%.
- 4. When necessary, Cypress packages semiconductor devices in highly moisture-resistant aluminum laminate bags, with a silica gel desiccant. Devices should be sealed in these aluminum laminate bags for storage.
- 5. Avoid storing packages where they are exposed to corrosive gases or high levels of dust.

Baking

Packages that have absorbed moisture may be de-moisturized by baking (heat drying). Follow the Cypress recommended conditions for baking.

Condition: 125°C/24 h

Static Electricity

Because semiconductor devices are particularly susceptible to damage by static electricity, you must take the following precautions:

- 1. Maintain relative humidity in the working environment between 40% and 70%. Use of an apparatus for ion generation may be needed to remove electricity.
- 2. Electrically ground all conveyors, solder vessels, soldering irons, and peripheral equipment.
- Eliminate static body electricity by the use of rings or bracelets connected to ground through high resistance (on the level of 1 MΩ). Wearing of conductive clothing and shoes, and the use of conductive floor mats and other measures to minimize shock loads is recommended.
- 4. Ground all fixtures and instruments, or protect with anti-static measures.
- 5. Avoid the use of Styrofoam or other highly static-prone materials for storage of completed board assemblies.

S6E2G Series



Memory Map (2)



*: See S6E2GM/GK/GH/G3/G2 Series Flash Programming Manual to confirm the detail of flash Memory.



11. Pin Status in Each CPU State

The terms used for pin status have the following meanings:

■ INITX = 0

This is the period when the INITX pin is at the L level.

■ INITX = 1

This is the period when the INITX pin is at the H level.

■ SPL = 0

This is the status that the standby pin level setting bit (SPL) in the standby mode control register (STB_CTL) is set to 0.

■ SPL = 1

This is the status that the standby pin level setting bit (SPL) in the standby mode control register (STB_CTL) is set to 1.

Input enabled

Indicates that the input function can be used.

Internal input fixed at 0

This is the status that the input function cannot be used. Internal input is fixed at L.

Hi-Z

Indicates that the pin drive transistor is disabled and the pin is put in the Hi-Z state.

Setting disabled

Indicates that the setting is disabled.

Maintain previous state

Maintains the state that was immediately prior to entering the current mode. If a built-in peripheral function is operating, the output follows the peripheral function. If the pin is being used as a port, that output is maintained.

Analog input is enabled

Indicates that the analog input is enabled.

Trace output

Indicates that the trace function can be used.

GPIO selected

In Deep standby mode, pins switch to the general-purpose I/O port.

Setting prohibition

Prohibition of a setting by specification limitation



tatus Type	Function Group	Power-On Reset or Low- Voltage Detection State	INITX Input State	Device Internal Reset State	Device Internal Reset State Run mode or Sleep State Run mode RTC mode, RTC mode, or State Stop mode State		Deep Sta mode or Do Stop mo	Return from Deep Standby mode State																							
Pin S		Power Supply Unstable	Power Sta	Supply ble	Power Supply Stable	Power Supply Stable		Power Supply Stable		Power Supply Stable																					
		-	INITX=0	INITX=1	INITX=1	INITX=1		INI	INITX=1																						
		-	-	-	-	SPL=0	SPL=1	SPL=0	SPL=1	-																					
	Analog output selected					*2	*3																								
J	External interrupt enable selected	Hi-Z	Hi-Z/ input	Hi-Z/	Hi-Z/	Maintain previous state	Maintain previous state		Maintain previous state	GPIO selected, internal input	Hi-Z/internal input fixed	GPIO selected																			
	Resource other than above selected		enabled	enabled	state			state	state	state	State	State	state	state	SIALE	state	state	state	State	State	Maintain previous state	Hi-Z/internal input fixed at 0	at 0								
	GPIO selected																														
	External interrupt enable selected	Setting disabled	Setting disabled	Setting disabled	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state		Maintain previous state	GPIO																				
к	Resource other than above selected	Hi-Z	Hi-Z/ input	Hi-Z/ input					Maintain previous state	previous state	previous state	previous state	Maintain previous state	Maintain previous state	previous state	previous state	previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state	Maintain previous state
	GPIO selected		enabled	nabled enabled			at 0																								
L	Analog input selected	Hi-Z	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled	Hi-Z/ internal input fixed at 0/ analog input enabled																					
	Resource other than above selected	Setting disabled	Setting disabled	Setting disabled	Maintain previous state	Maintain previous state	Hi-Z/internal input fixed at 0	GPIO selected, internal input fixed	Hi-Z/internal input fixed at 0	GPIO selected																					
	selected							atu																							





- 2: Vcc must not drop below Vss 0.5 V.
- 3: USBV_{CC}0, USBV_{CC}1 must not drop below V_{SS} 0.5 V.
- 4: ETHV_{CC} must not drop below V_{SS} 0.5 V.
- 5: Ensure that the voltage does not exceed V_{CC} + 0.5V, for example, when the power is turned on.
- 6: The maximum output current is defined as the value of the peak current flowing through any one of the corresponding pins.
- 7: The average output current is defined as the average current value flowing through any one of the corresponding pins for a 100-ms period.
- 8: The total average output current is defined as the average current value flowing through all of corresponding pins for a 100-ms period.

WARNING:

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Semiconductor devices may be permanently damaged by application of stress (including, without limitation, voltage, current or temperature) in excess of absolute maximum ratings. Do not exceed any of these ratings.



Current Explanation Diagram





Demonster	0	Pin	Conditions		Conditions		⊷	Va	lue	11	Dementer											
Parameter	Symbol	Name			rrequency**	Typ*1	Max* ²	Unit	Remarks													
				*5	180 MHz	82	140	mA														
					160 MHz	74	132	mA														
					144 MHz	68	126	mA														
					120 MHz	58	116	mA														
					100 MHz	49	107	mA	*3													
				*6	80 MHz	40	98	mA	When all peripheral													
				0	60 MHz	31	89	mA	clocks are on													
					40 MHz	22	80	mA]													
					Nie was ei	Nama	Normal operation		20 MHz	13	71	mA										
								Normal operation	Normal operation	Normal operation				8 MHz	7.5	65	mA					
Power	las l		laa	VCC	VCC	VCC						4 MHz	5.6	63	mA							
supply current	ICC	VCC	*7,*8 (PLL)	*5	180 MHz	48	106	mA														
											(1 LL)		160 MHz	44	102	mA						
																	-	144 MHz	41	99	mA	
																		120 MHz	35	93	mA	
			*6	*6	*6	*6		1		100 MHz	30	88	mA	*3								
								80 MHz	25	83	mA	When all peripheral										
												ΰb	60 MHz	20	78	mA	clocks are off					
					40 MHz	14	72	mA														
					20 MHz	8.7	66	mA														
					8 MHz	5.6	63	mA														
					4 MHz	4.5	62	mA														

Table 12-2 Typical and Maximum Current Consumption in Normal Operation (PLL), Code with Data Accessing Running from Flash Memory (Flash Accelerator Mode and Trace Buffer Function Disabled)

1: T_A = +25 °C, V_{CC} = 3.3 V

2: T_J = +125 °C, V_{CC} = 5.5 V

3: When all ports are input and are fixed at 0

4: Frequency is a value of HCLK when PCLK0 = PCLK1 = PCLK2 = HCLK

5: When stopping flash accelerator mode and trace buffer function (FRWTR.RWT = 11, FBFCR.BE = 0)

6: When stopping flash accelerator mode and trace buffer function (FRWTR.RWT = 10, FBFCR.BE = 0)

7: With data access to a MainFlash memory.

8: When using the crystal oscillator of 4 MHz (including the current consumption of the oscillation circuit)



-	•	Pin															
Parameter	Symbol	Name	Conditions	Frequency	Typ* ¹	Max* ²	Unit	Remarks									
			Deen standby		89	162	μA	*3, *4 T _A = +25°C									
			Stop mode (When RAM	-	-	1689	μA	*3, *4 T _A = +85°C									
	1		is off)		-	2189	μA	*3, *4 T _A = +105°C									
	ICCHD	- vcc	Deep standby		101	245	μA	*3, *4 T _A = +25°C									
			Stop mode (When RAM is on)	Stop mode (When RAM	Stop mode (When RAM	Stop mode (When RAM	Stop mode (When RAM	Stop mode (When RAM	Stop mode (When RAM	Stop mode (When RAM	Stop mode (When RAM	Stop mode (When RAM	ode RAM	-	2401	μA	*3, *4 T _A = +85°C
Power					-	3223	μA	*3, *4 T _A = +105°C									
current			Deep standby RTC mode ^{*6} (When RAM is off) Deep standby RTC mode ^{*6} (When RAM is on)		93	166	μA	*3, *4 T _A = +25°C									
				RTC mode*6 (When RAM is off)	RTC mode ^{*6} (When RAM is off)	RTC mode*6 (When RAM is off)	RTC mode ^{*6} (When RAM is off)	RTC mode ^{*6} (When RAM is off) 32 kHz	RTC mode ^{*6} (When RAM		-	1693	μA	*3, *4 T _A = +85°C			
										-	2193	μA	*3, *4 T _A = +105°C				
	ICCRD								32 kHz	105	249	μA	*3, *4 T _A = +25°C				
				C mode ^{*6} nen RAM	-	2405	μA	*3, *4 T _A = +85°C									
					-	3227	μA	*3, *4 T _A = +105°C									

Table 12-9 Typical and Maximum Current Consumption in Deep Standby Stop Mode, Deep Standby RTC Mode

1: Vcc = 3.3 V

2: Vcc = 5.5 V

3: When all ports are input and are fixed at 0

4: When LVD is off

5: When sub oscillation is off

6: When using the crystal oscillator of 32 kHz (including the current consumption of the oscillation circuit)



12.8 MainFlash Memory Write/Erase Characteristics

 $(V_{CC} = 2.7V \text{ to } 5.5V)$

Devenuerten			Value		11	Demerler	
Pa	Min	Тур	Мах	Unit	Remarks		
Contax areas time	Large Sector	-	0.7	3.7	s	Includes write time prior to internal	
Sector erase time	Small Sector	-	0.3	1.1	S	erase	
Half word (16-bit)	Write cycles < 100 times		12	100		Not including system-level overhead	
write time	Write cycles > 100 times	-		200	μs	time	
Chip erase time*		-	13.6	68	S	Includes write time prior to internal erase	

 $\ensuremath{^*\!:}$ It indicates the chip erase time of 1MB MainFlash memory

For devices with 1.5 MB or 2 MB of MainFlash memory, two erase cycles are required.

See 3.2.2 Command Operating Explanations and 3.3.3 Flash Erase Operation in this product's Flash Programming Manual for the detail.

Write Cycles and Data Retention Time

Erase/Write Cycles (Cycle)	Data Retention Time (Year)
1,000	20*
10,000	10*
100,000	5*

*: This value comes from the technology qualification (using Arrhenius equation to translate high temperature acceleration test result into average temperature value at + 85°C).





Example of Standby Recovery Operation (when in Internal Resource Interrupt Recovery*)

*: Depending on the standby mode, interrupt from the internal resource is not included in the recovery cause.

Notes:

- The return factor is different in each low-power consumption mode. See Chapter 6: Low Power Consumption mode and Operations of Standby modes in FM4 Family Peripheral Manual Main Part (002-04856).
- The recovery process is unique for each operating mode. See Chapter 6: Low Power Consumption mode in FM4 Family Peripheral Manual Main Part (002-04856).



Internal Resource RST Internal RST RST Active tront CPU Operation Start

Example of Standby Recovery Operation (when in Internal Resource Reset Recovery*)

*: Depending on the low-power consumption mode, the reset issue from the internal resource is not included in the recovery cause.

Notes:

- The return factor is different in each low power consumption mode.
 See Chapter 6: Low Power Consumption mode and Operations of Standby modes in "FM4 Family Peripheral Manual Main Part (002-04856).
- The recovery process is unique for each operating mode. See Chapter 6: Low Power Consumption mode in FM4 Family Peripheral Manual Main Part (002-04856).
- When the power-on reset/low-voltage detection reset, they are not included in the return factor. See 12.4.8 Power-On Reset Timing.
- In recovering from reset, CPU changes to High-speed Run mode. In the case of using the main clock and PLL clock, they need further main clock oscillation stabilization wait time and oscillation stabilization wait time of Main PLL clock.
- Internal resource reset indicates Watchdog reset and CSV reset.



14. Package Dimensions

